# 2SC4927

# Silicon NPN Triple Diffused

# **HITACHI**

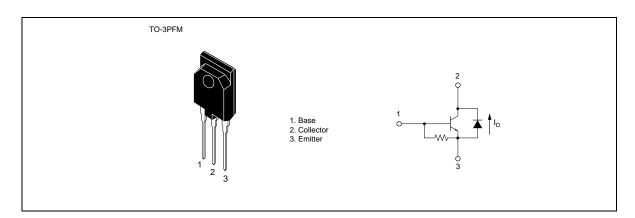
### **Application**

TV/character display horizontal deflection output

#### **Features**

- High breakdown voltage
  - $V_{\scriptscriptstyle CES} = 1500~V$
- Built-in damper diode type
- Isolated package TO-3PFM

#### Outline



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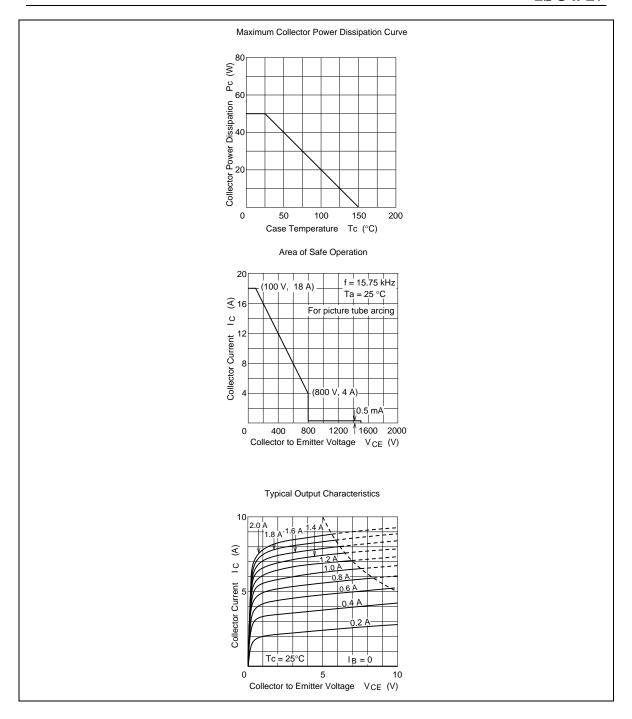
### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

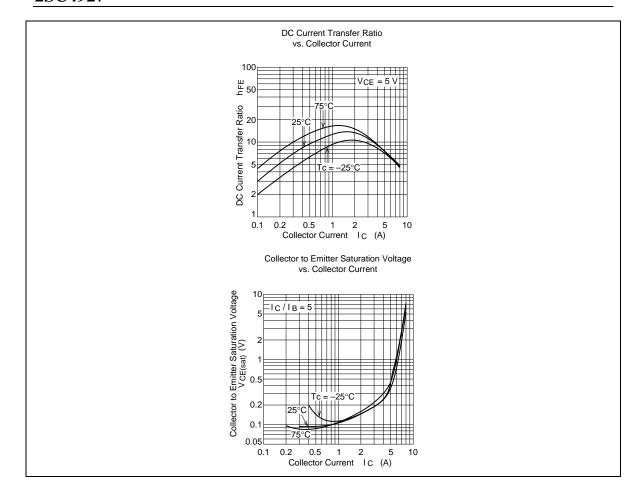
Item	Symbol	Ratings	Unit	
Collector to emitter voltage	V <sub>CES</sub>	1500	V	
Emitter to base voltage	$V_{\scriptscriptstyle{EBO}}$	6	V	
Collector current	I <sub>c</sub>	8	A	,
Collector peak current	I <sub>C(peak)</sub>	9	A	
Collector surge current	l <sub>C(surge)</sub>	18	A	
Collector power dissipation	P <sub>c</sub> *1	50	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
C to E diode forward current	I <sub>D</sub>	8	A	

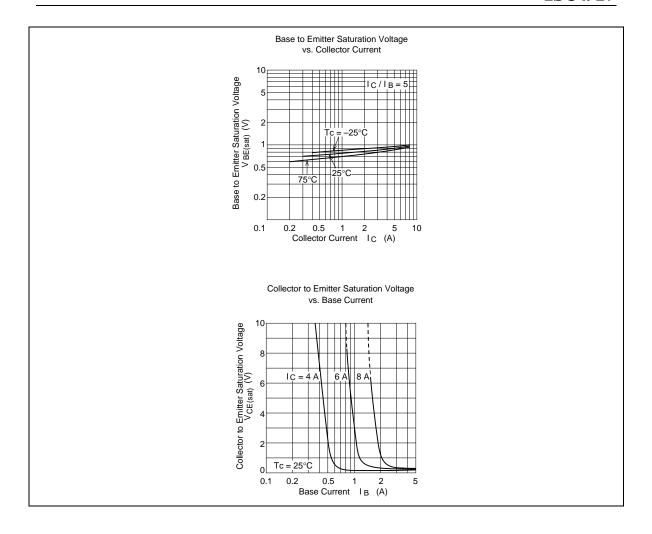
Note: 1. Value at  $T_c = 25$ °C.

### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{\text{(BR)EBO}}$	6	_	_	V	$I_{\rm E} = 500 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I <sub>CES</sub>	_	_	500	μΑ	V <sub>CE</sub> = 1500 V, R <sub>BE</sub> = 0
DC current transfer ratio	h <sub>FE</sub>	_	_	25	_	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$
Collector to emitter saturation voltage	$V_{\scriptscriptstyle{CE(sat)}}$	_	_	5	V	$I_{c} = 6 \text{ A}, I_{B} = 1.2 \text{ A}$
Base to emitter saturation voltage	$V_{_{BE(sat)}}$	_	_	1.5	V	$I_{c} = 6 \text{ A}, I_{B} = 1.2 \text{ A}$
C to E diode forward voltage	$V_{\text{ECF}}$	_	_	2.0	V	I <sub>F</sub> = 8 A
Fall time	t <sub>f</sub>	_	_	0.5	μs	$I_{CP} = 6 \text{ A}, I_{B1} = 1.2 \text{ A},$ $I_{B2} \cong -2.4 \text{ A}, f_{H} = 31.5 \text{ kHz}$







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